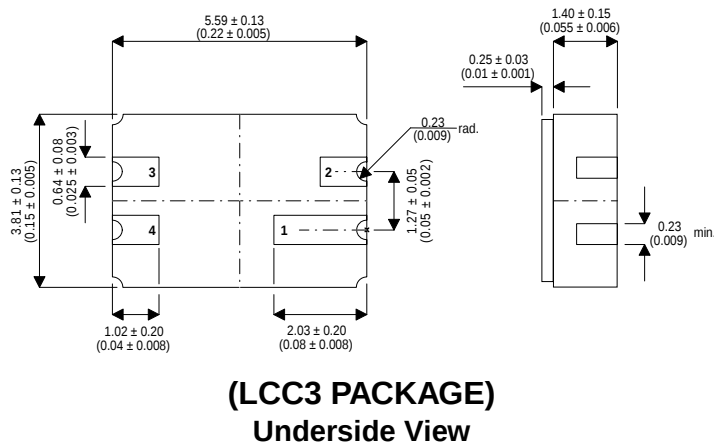


MECHANICAL DATA

Dimensions in mm (inches)



PAD 1 — Cathode PAD 3 — No Connection
PAD 2 — No Connection PAD 4 — Anode

GENERAL PURPOSE SILICON RECTIFIER DIODE

General Purpose Rectifier Diode
In Hermetic Ceramic Surface Mount Package
For High Reliability Applications

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_R Reverse Voltage				200	V
V_{RRM} Peak Reverse Voltage				200	V
$I_{F(AV)}$ Average Half Wave Rectified Forward Current	$T_{amb} \leq 25^{\circ}\text{C}$			1.0	A
	$T_{amb} = 100^{\circ}\text{C}$			0.75	
I_F D.C Forward Current				1	A
I_{FRM} Repetitive Peak Forward Current				10	A
I_{FSM} Non-Repetitive Peak Forward Current	(half cycle surge , 60 c.p.s)			30	A

T_{stg} Storage Temperature Range	-55 to +175 $^{\circ}\text{C}$
T_j Max junction temperature	+150 $^{\circ}\text{C}$

CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F Forward Voltage Drop	$I_F = 1\text{A}$			1.1	V
$V_{F(AV)}$ Full-Cycle average forward voltage drop	$I_{F(AV)} = 1\text{A}$			0.8	V
I_R Reverse Current	$V_R = 50\text{V}$, $T_{amb} = 25^{\circ}\text{C}$			10	μA
	$V_R = 50\text{V}$, $T_{amb} = 100^{\circ}\text{C}$			50	
$I_{R(AV)}$ Full cycle average reverse current	$V_{RRM} = 50\text{V}$, $T_{amb} = 75^{\circ}\text{C}$			30	μA